

# Luigi Mariucci

## List of Publications by Year in descending order

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docs citations

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times ranked

1814  
citing authors

| #  | ARTICLE  | IF  | CITATIONS |
|----|--|-----|-----------|
| 1  | Low-temperature polysilicon thin film transistors on polyimide substrates for electronics on plastic. Solid-State Electronics, 2008, 52, 348-352.  | 0.8 | 122       |
| 2  | High performance printed N and P-type OTFTs enabling digital and analog complementary circuits on flexible plastic substrate. Solid-State Electronics, 2013, 84, 167-178.  | 0.8 | 72        |
| 3  | High-field-effect-mobility pentacene thin-film transistors with polymethylmetacrylate buffer layer. Applied Physics Letters, 2005, 86, 203505.   | 1.5 | 70        |
| 4  | Dopant redistribution and electrical activation in silicon following ultra-low energy boron implantation and excimer laser annealing. Physical Review B, 2003, 67, .   | 1.1 | 60        |
| 5  | Contact effects in high performance fully printed p-channel organic thin film transistors. Applied Physics Letters, 2011, 99, .  | 1.5 | 60        |
| 6  | Kink effect in short-channel polycrystalline silicon thin-film transistors. Applied Physics Letters, 2004, 85, 3113-3115.  | 1.5 | 56        |
| 7  | Hot carrier effects in n-channel polycrystalline silicon thin-film transistors: a correlation between off-current and transconductance variations. IEEE Transactions on Electron Devices, 1994, 41, 340-346.   | 1.6 | 54        |
| 8  | â€œHumpâ€•characteristics and edge effects in polysilicon thin film transistors. Journal of Applied Physics, 2008, 104, .  | 1.1 | 54        |
| 9  | Aging effects in pentacene thin-film transistors: Analysis of the density of states modification. Applied Physics Letters, 2006, 88, 193508.   | 1.5 | 48        |
| 10 | Current spreading effects in fully printed p-channel organic thin film transistors with Schottky sourceâ€•drain contacts. Organic Electronics, 2013, 14, 86-93.  | 1.4 | 44        |
| 11 | Surface-scattering effects in polycrystalline silicon thin-film transistors. Applied Physics Letters, 2003, 82, 3119-3121.   | 1.5 | 43        |
| 12 | Polysilicon TFT Structures for Kink-Effect Suppression. IEEE Transactions on Electron Devices, 2004, 51, 1135-1142.  | 1.6 | 40        |
| 13 | Lateral growth control in excimer laser crystallized polysilicon. Thin Solid Films, 1999, 337, 137-142.  | 0.8 | 39        |
| 14 | Controlling field-effect mobility in pentacene-based transistors by supersonic molecular-beam deposition. Applied Physics Letters, 2006, 88, 132106.   | 1.5 | 39        |
| 15 | Determination of hot-carrier induced interface state density in polycrystalline silicon thin-film transistors. Journal of Applied Physics, 1998, 84, 2341-2348.  | 1.1 | 37        |
| 16 | Ultra-shallow junction formation by excimer laser annealing and low energy (<1 keV) B implantation: A two-dimensional analysis. Nuclear Instruments & Methods in Physics Research B, 2002, 186, 401-408.   | 0.6 | 36        |
| 17 | Principle of operation and modeling of source-gated transistors. Journal of Applied Physics, 2013, 114, .  | 1.1 | 35        |
| 18 | Redistribution and electrical activation of ultralow energy implanted boron in silicon following laser annealing. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2002, 20, 644. | 1.6 | 34        |

| #  | ARTICLE  | IF  | CITATIONS |
|----|--|-----|-----------|
| 19 | Carbon nanotube semitransparent electrodes for amorphous silicon based photovoltaic devices. Applied Physics Letters, 2011, 98, .  | 1.5 | 34        |
| 20 | Variation-based design of an AM demodulator in a printed complementary organic technology. Organic Electronics, 2014, 15, 904-912.   | 1.4 | 34        |
| 21 | Unified drain-current model of complementary p- and n-type OTFTs. Organic Electronics, 2015, 22, 5-11.   | 1.4 | 34        |
| 22 | Two-dimensional delineation of ultrashallow junctions obtained by ion implantation and excimer laser annealing. Applied Physics Letters, 2000, 77, 552-554.  | 1.5 | 33        |
| 23 | Analysis of contact effects in fully printed p-channel organic thin film transistors. Organic Electronics, 2012, 13, 2017-2027.  | 1.4 | 33        |
| 24 | Aging effects and electrical stability in pentacene thin film transistors. Thin Solid Films, 2007, 515, 7546-7550.   | 0.8 | 31        |
| 25 | Pentacene TFTs with parylene passivation layer. Thin Solid Films, 2009, 517, 6283-6286.  | 0.8 | 31        |
| 26 | Depth distribution of B implanted in Si after excimer laser irradiation. Applied Physics Letters, 2005, 86, 051909.  | 1.5 | 29        |
| 27 | Numerical analysis of electrical characteristics of polysilicon thin film transistors fabricated by excimer laser crystallisation. Electronics Letters, 1998, 34, 924.   | 0.5 | 28        |
| 28 | Analysis of electrical characteristics of gate overlapped lightly doped drain (GOLDD) polysilicon thin-film transistors with different LDD doping concentration. IEEE Transactions on Electron Devices, 2003, 50, 2425-2433. | 1.6 | 28        |
| 29 | Crystallization mechanisms in laser irradiated thin amorphous silicon films. Thin Solid Films, 2003, 427, 91-95.   | 0.8 | 27        |
| 30 | Effect of active layer thickness on electrical characteristics of pentacene TFTs with PMMA buffer layer. Solid-State Electronics, 2008, 52, 412-416.   | 0.8 | 27        |
| 31 | Short channel effects in polysilicon thin film transistors. Thin Solid Films, 2005, 487, 221-226.  | 0.8 | 26        |
| 32 | Contact Effects in Amorphous InGaZnO Thin Film Transistors. Journal of Display Technology, 2014, 10, 956-961.  | 1.3 | 25        |
| 33 | Analysis of self-heating related instability in n-channel polysilicon thin film transistors fabricated on polyimide. Thin Solid Films, 2009, 517, 6371-6374.   | 0.8 | 24        |
| 34 | Fabrication and nonlinear characterization of GaN HEMTs on SiC and sapphire for high-power applications. International Journal of RF and Microwave Computer-Aided Engineering, 2006, 16, 70-80.                              | 0.8 | 23        |
| 35 | A Two-Pass Excimer Laser Annealing Process to Control Amorphous Silicon Crystallization. Japanese Journal of Applied Physics, 1999, 38, L907-L910.   | 0.8 | 22        |
| 36 | Advanced excimer laser crystallization techniques. Thin Solid Films, 2001, 383, 39-44.   | 0.8 | 22        |

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|----|--|-----|-----------|
| 37 | Material modifications induced by laser annealing in two-dimensional structures. Applied Physics Letters, 2004, 84, 4738-4740.   | 1.5 | 22        |
| 38 | Low-temperature, self-catalyzed growth of Si nanowires. Nanotechnology, 2010, 21, 255601.  | 1.3 | 22        |
| 39 | Dispersive charge injection model for hydrogenated amorphous silicon/amorphous silicon dioxide thin-film transistor instability. Applied Physics Letters, 1991, 59, 826-828.                         | 1.5 | 21        |
| 40 | Hot-carrier-induced degradation of LDD polysilicon TFTs. IEEE Transactions on Electron Devices, 2006, 53, 43-50.   | 1.6 | 21        |
| 41 | Low-Temperature Annealing Combined with Laser Crystallization for Polycrystalline Silicon TFTs on Polymeric Substrate. Journal of the Electrochemical Society, 2008, 155, H764.                      | 1.3 | 21        |
| 42 | Self-heating effects in polycrystalline silicon thin film transistors. Applied Physics Letters, 2006, 89, 093509.  | 1.5 | 20        |
| 43 | Threshold voltage in short channel polycrystalline silicon thin film transistors: Influence of drain induced barrier lowering and floating body effects. Journal of Applied Physics, 2010, 107, .    | 1.1 | 20        |
| 44 | Temperature dependence of the transfer characteristics of polysilicon thin film transistors fabricated by excimer laser crystallization. Journal of Applied Physics, 1999, 85, 616-618.              | 1.1 | 19        |
| 45 | Light polarization control in strain-engineered GaAsN/GaAsN:H heterostructures. Applied Physics Letters, 2009, 94, 261905.   | 1.5 | 19        |
| 46 | Influence of structural properties on environmental stability of pentacene thin film transistors. Organic Electronics, 2011, 12, 447-452.  | 1.4 | 19        |
| 47 | Excimer laser crystallization techniques for polysilicon TFTs. Applied Surface Science, 2000, 154-155, 95-104.   | 3.1 | 18        |
| 48 | High performance printed N and P-type OTFTs for complementary circuits on plastic substrate. , 2012, , .   |     | 18        |
| 49 | A novel fabrication process for polysilicon thin film transistors with source/drain contacts formed by deposition and lift-off of highly doped layers. Solid-State Electronics, 2002, 46, 1351-1358. | 0.8 | 17        |
| 50 | Analysis of Self-Heating-Related Instability in Self-Aligned p-Channel Polycrystalline-Silicon Thin-Film Transistors. IEEE Electron Device Letters, 2010, 31, 830-832.                               | 2.2 | 17        |
| 51 | Evidence of Correlated Mobility Fluctuations in p-Type Organic Thin-Film Transistors. IEEE Electron Device Letters, 2015, 36, 390-392.   | 2.2 | 17        |
| 52 | Numerical Analysis of the Electrical Characteristics of Gate Overlapped Lightly Doped Drain Polysilicon Thin Film Transistors. Japanese Journal of Applied Physics, 1999, 38, 3475-3481.             | 0.8 | 16        |
| 53 | Pentacene thin film transistors with (polytetrafluoroethylene) PTFE-like encapsulation layer. Organic Electronics, 2011, 12, 119-124.  | 1.4 | 16        |
| 54 | A Compact SPICE Model for Organic TFTs and Applications to Logic Circuit Design. IEEE Nanotechnology Magazine, 2016, 15, 754-761.  | 1.1 | 16        |

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|----|--|-----|-----------|
| 55 | A DC and small signal AC model for organic thin film transistors including contact effects and non quasi static regime. <i>Organic Electronics</i> , 2017, 41, 345-354.                            | 1.4 | 16        |
| 56 | Hot carrier-induced degradation of gate overlapped lightly doped drain (GOLDD) polysilicon TFTs. <i>IEEE Transactions on Electron Devices</i> , 2002, 49, 636-642.                                 | 1.6 | 15        |
| 57 | The effect of excimer laser pretreatment on diffusion and activation of boron implanted in silicon. <i>Applied Physics Letters</i> , 2005, 87, 192109.   | 1.5 | 15        |
| 58 | Analysis of electrical characteristics of high performance pentacene thin-film transistors with PMMA buffer layer. <i>Journal of Non-Crystalline Solids</i> , 2006, 352, 1765-1768.                | 1.5 | 15        |
| 59 | Excimer Laser annealing for shallow junction formation in Si power MOS devices. <i>Thin Solid Films</i> , 2006, 504, 2-6.  | 0.8 | 15        |
| 60 | Modeling of Capacitance Characteristics of Printed p-Type Organic Thin-Film Transistors. <i>IEEE Transactions on Electron Devices</i> , 2014, 61, 4120-4127.                                       | 1.6 | 15        |
| 61 | Three-dimensional characterization of OTFT on modified hydrophobic flexible polymeric substrate by low energy Cs <sup>+</sup> ion sputtering. <i>Applied Surface Science</i> , 2018, 448, 628-635. | 3.1 | 15        |
| 62 | Gravure printed organic thin film transistors: Study on the ink printability improvement. <i>Organic Electronics</i> , 2018, 61, 104-112.  | 1.4 | 15        |
| 63 | Low voltage operation a-Si:H thin film transistors with very thin PECVD a-SiO <sub>2</sub> gate dielectric. <i>Journal of Non-Crystalline Solids</i> , 1989, 115, 144-146.                         | 1.5 | 14        |
| 64 | Electrical stability in self-aligned p-channel polysilicon thin film transistors. <i>Thin Solid Films</i> , 2007, 515, 7571-7575.  | 0.8 | 14        |
| 65 | Effect of hydrogen incorporation temperature in plane-engineered GaAsN <sup>x</sup> /GaAsN:H heterostructures. <i>Applied Physics Letters</i> , 2008, 92, 221901.                                  | 1.5 | 14        |
| 66 | Design of analog and digital building blocks in a fully printed complementary organic technology. , 2012, , .  |     | 14        |
| 67 | Fabrication of ultra-shallow junctions with high electrical activation by excimer laser annealing. <i>Materials Science in Semiconductor Processing</i> , 2001, 4, 417-423.                        | 1.9 | 13        |
| 68 | Integration of Melting Excimer Laser Annealing in Power MOS Technology. <i>IEEE Transactions on Electron Devices</i> , 2007, 54, 852-860.  | 1.6 | 13        |
| 69 | Self-heating effects on the electrical instability of fully printed p-type organic thin film transistors. <i>Applied Physics Letters</i> , 2012, 101, .  | 1.5 | 13        |
| 70 | Highly sensitive organic phototransistor for flexible optical detector arrays. <i>Organic Electronics</i> , 2022, 102, 106452.   | 1.4 | 13        |
| 71 | SuMBE based organic thin film transistors. <i>Synthetic Metals</i> , 2004, 146, 291-295.   | 2.1 | 12        |
| 72 | Stable p-channel polysilicon thin film transistors fabricated by laser doping technique. <i>Thin Solid Films</i> , 2005, 487, 232-236.   | 0.8 | 12        |

| #  | ARTICLE  | IF  | CITATIONS |
|----|--|-----|-----------|
| 73 | Grain boundary evaluation in sequentially laterally solidified polycrystalline-silicon devices. Journal of Applied Physics, 2007, 101, 094502.   | 1.1 | 12        |
| 74 | A new self-consistent model for the analysis of hot-carrier induced degradation in lightly doped drain (LDD) and gate overlapped LDD polysilicon TFTs. Thin Solid Films, 2003, 427, 117-122.     | 0.8 | 11        |
| 75 | Electrical activation phenomena induced by excimer laser annealing in B-implanted silicon. Applied Physics Letters, 2004, 85, 2268-2270.   | 1.5 | 11        |
| 76 | Role of gate oxide thickness in controlling short channel effects in polycrystalline silicon thin film transistors. Applied Physics Letters, 2009, 95, .   | 1.5 | 11        |
| 77 | Correlated Mobility Fluctuations and Contact Effects in p-Type Organic Thin-Film Transistors. IEEE Transactions on Electron Devices, 2016, 63, 1239-1245.  | 1.6 | 11        |
| 78 | Numerical simulation of parasitic resistance effects in polycrystalline silicon TFTs. IEEE Transactions on Electron Devices, 2006, 53, 573-577.  | 1.6 | 10        |
| 79 | Giant and reversible enhancement of the electrical resistance of GaAs $1-x$ N $x$ by hydrogen irradiation. Physical Review B, 2011, 84, .  | 1.1 | 10        |
| 80 | Analysis of short channel effects in poly-Si thin film transistors: A new method. Microelectronic Engineering, 1992, 19, 183-186.  | 1.1 | 9         |
| 81 | Hot carrier effects in polycrystalline silicon thin-film transistors: analysis of electrical characteristics and noise performance modifications. Microelectronics Reliability, 1999, 39, 45-52. | 0.9 | 9         |
| 82 | Enhanced boron diffusion in excimer laser preannealed Si. Applied Physics Letters, 2005, 86, 151902.   | 1.5 | 9         |
| 83 | Hot-carrier effects in p-channel polycrystalline silicon thin film transistors. Applied Physics Letters, 2006, 89, 183518.   | 1.5 | 9         |
| 84 | In-plane band gap modulation investigated by secondary electron imaging of GaAsN/GaAsN:H heterostructures. Applied Physics Letters, 2008, 93, 102116.  | 1.5 | 9         |
| 85 | Space-charge photomodulation in metal/insulator/amorphous semiconductor structures (TFTs). IEEE Transactions on Electron Devices, 1989, 36, 2825-2828.   | 1.6 | 8         |
| 86 | Hydrogenated amorphous silicon technology for chemically sensitive thin-film transistors. Sensors and Actuators B: Chemical, 1992, 6, 29-33.   | 4.0 | 8         |
| 87 | Determination of excess current due to impact ionization in polycrystalline silicon thin-film transistors. Solid-State Electronics, 1998, 42, 613-618.   | 0.8 | 8         |
| 88 | Boron distribution in silicon after multiple pulse excimer laser annealing. Applied Physics Letters, 2005, 87, 081901.   | 1.5 | 8         |
| 89 | Modelling velocity saturation and kink effects in p-channel polysilicon thin-film transistors. Thin Solid Films, 2007, 515, 7417-7421.   | 0.8 | 8         |
| 90 | Effective channel length and parasitic resistance determination in non self-aligned low temperature polycrystalline silicon thin film transistors. Thin Solid Films, 2009, 517, 6353-6357.       | 0.8 | 8         |

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|-----|---|-----|-----------|
| 91  | Quantum confinement effects in hydrogen-intercalated Ga <sub>1-x</sub> As <sub>x</sub> N <sub>x</sub> -GaAs <sub>1-x</sub> N <sub>x</sub> :H planar heterostructures investigated by photoluminescence spectroscopy. <i>Physical Review B</i> , 2010, 81, . | 1.1 | 8         |
| 92  | The Role of Defective Regions Near the Contacts on the Electrical Characteristics of Bottom-Gate Bottom-Contact Organic TFTs. <i>Journal of Display Technology</i> , 2016, 12, 252-257.   | 1.3 | 8         |
| 93  | Dual-ion-beam sputtering technique for the production of hydrogenated amorphous silicon. <i>Thin Solid Films</i> , 1984, 120, 215-222.  | 0.8 | 7         |
| 94  | a - Si <sub>1-x</sub> Ge <sub>x</sub> : H alloys for solar cells. <i>Journal of Non-Crystalline Solids</i> , 1987, 97-98, 1075-1078.  | 1.5 | 7         |
| 95  | Transport properties of plasma-deposited amorphous silicon dioxide. <i>Journal of Non-Crystalline Solids</i> , 1989, 115, 123-125.  | 1.5 | 7         |
| 96  | Density of states and photoconductivity light degradation in a-Si:H at different temperatures. <i>Journal of Non-Crystalline Solids</i> , 1996, 198-200, 482-485.   | 1.5 | 7         |
| 97  | Electrical characterization of directionally solidified polycrystalline silicon. <i>Journal of Applied Physics</i> , 2005, 98, 033702.  | 1.1 | 7         |
| 98  | Interdigitated sensorial system on flexible substrate. , 2008, , .  |     | 7         |
| 99  | A large signal non quasi static model of printed organic TFTs and simulation of CMOS circuits. , 2017, , .  |     | 7         |
| 100 | Experimental and theoretical evidence of space-charge photomodulation in metal/insulator/amorphous semiconductor structures. <i>Journal of Non-Crystalline Solids</i> , 1989, 114, 378-380.   | 1.5 | 6         |
| 101 | Source-Drain Metal Contact Effects in Short-Channel a-Si:H Thin-Film Transistors. <i>Japanese Journal of Applied Physics</i> , 1990, 29, L2353-L2356.   | 0.8 | 6         |
| 102 | Observation of super lateral growth in long pulse (170 ns) excimer laser crystallization of a-Si films. <i>Thin Solid Films</i> , 2003, 427, 319-323.   | 0.8 | 6         |
| 103 | Modelling Velocity Saturation Effects in Polysilicon Thin-Film Transistors. <i>Japanese Journal of Applied Physics</i> , 2006, 45, 4374-4377.   | 0.8 | 6         |
| 104 | Role of field enhanced mechanisms and impact ionization on the threshold voltage of short channel polycrystalline silicon thin film transistors. <i>Applied Physics Letters</i> , 2008, 93, 193512.   | 1.5 | 6         |
| 105 | Negative biasâ€“temperature stress in non-self-aligned p-channel polysilicon TFTs. <i>Thin Solid Films</i> , 2009, 517, 6379-6382.  | 0.8 | 6         |
| 106 | Downscaling effects on self-heating related instabilities in p-channel polycrystalline silicon thin film transistors. <i>Applied Physics Letters</i> , 2011, 99, .  | 1.5 | 6         |
| 107 | Analysis of Kink Effect and Short Channel Effects in Fully Self-Aligned Gate Overlapped Lightly Doped Drain Polysilicon TFTs. <i>Journal of Display Technology</i> , 2013, 9, 764-769.  | 1.3 | 6         |
| 108 | A compact Spice model for organic TFTs and applications to logic circuit design. , 2015, , .  |     | 6         |

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|-----|---|-----|-----------|
| 109 | Hybrid Electrothermal Simulations of GaN HEMT Devices Based on Self-Heating Free Virtual Electrical Characteristics. IEEE Transactions on Electron Devices, 2021, 68, 3740-3747.                  | 1.6 | 6         |
| 110 | Effects of tunneling on a-Si:H Schottky barriers. Journal of Applied Physics, 1987, 62, 3285-3287.  | 1.1 | 5         |
| 111 | Study of the defects induced by low-energy (100 eV) hydrogen ions on amorphous silicon dioxide. Applied Physics Letters, 1992, 60, 1564-1566.   | 1.5 | 5         |
| 112 | Hot-hole-induced degradation in polycrystalline silicon thin-film transistors: experimental and theoretical analysis. IET Circuits, Devices and Systems, 1994, 141, 33.                           | 0.6 | 5         |
| 113 | Temperature analysis of polysilicon thin-film transistors made by excimer laser crystallization. Thin Solid Films, 1999, 337, 196-199.  | 0.8 | 5         |
| 114 | Low-frequency noise in gate overlapped lightly doped drain polycrystalline silicon thin-film transistors. Applied Physics Letters, 2000, 76, 3268-3270.   | 1.5 | 5         |
| 115 | Lateral growth control by thickness spatial modulation of amorphous silicon film. Thin Solid Films, 2003, 427, 314-318.   | 0.8 | 5         |
| 116 | Noise performance of polycrystalline silicon thin-film transistors made by sequential lateral solidification. Applied Physics Letters, 2003, 82, 2709-2711.                                       | 1.5 | 5         |
| 117 | Improved electrical stability in asymmetric fingered polysilicon thin film transistors. Applied Physics Letters, 2006, 89, 123506.  | 1.5 | 5         |
| 118 | Flexible PVDF-TrFE Pyroelectric Sensor Integrated on a Fully Printed P-channel Organic Transistor. Procedia Engineering, 2012, 47, 526-529.   | 1.2 | 5         |
| 119 | Reduction of Short Channel Effects and Hot Carrier Induced Instability in Fully Self-Aligned Gate Overlapped Lightly Doped Drain Polysilicon TFTs. Journal of Display Technology, 2012, 8, 18-22. | 1.3 | 5         |
| 120 | Fully-organic flexible tactile sensor for advanced robotic applications. , 2014, , .  |     | 5         |
| 121 | Pd-Gate a-Si:H Thin-Film Transistors as Hydrogen Sensors. Japanese Journal of Applied Physics, 1990, 29, L2357-L2359.   | 0.8 | 4         |
| 122 | Hot-carrier-induced modifications to the noise performance of polycrystalline silicon thin-film transistors. Applied Physics Letters, 1997, 71, 1216-1218.  | 1.5 | 4         |
| 123 | Channel doping effects in poly-Si thin film transistors. Thin Solid Films, 2005, 487, 242-246.  | 0.8 | 4         |
| 124 | Dopant and defect interactions in polycrystalline silicon thin-film transistors. Journal of Applied Physics, 2005, 97, 104515.  | 1.1 | 4         |
| 125 | Very High Performance GaN HEMT devices by Optimized Buffer and Field Plate Technology. , 2006, , .  |     | 4         |
| 126 | Hot Carrier Effects in p-Channel Polycrystalline Silicon Thin Film Transistors Fabricated on Flexible Substrates. Japanese Journal of Applied Physics, 2007, 46, 1299-1302.                       | 0.8 | 4         |



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|-----|---|-----|-----------|
| 127 | Insight into excimer laser crystallization exploiting ellipsometry: Effect of silicon film precursor. Thin Solid Films, 2007, 515, 7508-7512.   | 0.8 | 4         |
| 128 | Growth and Manipulation of Organic Semiconductors Microcrystals by Wet Lithography. Advanced Functional Materials, 2016, 26, 2387-2393.   | 7.8 | 4         |
| 129 | Hydrogen effects on a-SiO <sub>2</sub> : A photoemission study. Journal of Non-Crystalline Solids, 1991, 137-138, 1079-1082.  | 1.5 | 3         |
| 130 | Hot carriers effects in polycrystalline silicon thin-film transistors. Microelectronic Engineering, 1992, 19, 109-112.  | 1.1 | 3         |
| 131 | Excimer laser annealing of shallow As and B doped layers. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2004, 114-115, 352-357.   | 1.7 | 3         |
| 132 | Excimer laser annealing of B and BF <sub>2</sub> implanted Si. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2005, 124-125, 232-234.  | 1.7 | 3         |
| 133 | Improved electrical stability in asymmetric fingered polysilicon thin film transistors. Thin Solid Films, 2005, 487, 237-241.   | 0.8 | 3         |
| 134 | Annealing temperature effects on the electrical characteristics of p-channel polysilicon thin film transistors. Journal of Non-Crystalline Solids, 2006, 352, 1723-1727.  | 1.5 | 3         |
| 135 | Electrical instability in self-aligned p-channel polysilicon TFTs related to damaged regions present at the gate edges. Solid-State Electronics, 2008, 52, 406-411.   | 0.8 | 3         |
| 136 | (Invited) Downscaling Issues in Polycrystalline Silicon TFTs. ECS Transactions, 2010, 33, 3-22.   | 0.3 | 3         |
| 137 | (Invited) Contact Effects in Organic Thin Film Transistors with Different Device Structures. ECS Transactions, 2014, 64, 131-142.   | 0.3 | 3         |
| 138 | Graphene-based field effect transistors for radiation-induced field sensing. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 2016, 824, 392-393. | 0.7 | 3         |
| 139 | Theoretical Analysis of a-Si:H Based Multilayer Structure Thin Film Transistors. Japanese Journal of Applied Physics, 1990, 29, 1634-1638.  | 0.8 | 2         |
| 140 | Chemically sensitive hydrogenated amorphous silicon thin-film transistors. Journal of Non-Crystalline Solids, 1991, 137-138, 1253-1256.   | 1.5 | 2         |
| 141 | Application of the photo induced discharge technique for the investigation of a-Si:H thin-film transistor instability. Journal of Non-Crystalline Solids, 1993, 164-166, 735-738.   | 1.5 | 2         |
| 142 | <title>High-electric-field phenomena in polycrystalline silicon thin film transistors</title>. , 1997, , .  |     | 2         |
| 143 | Excess noise in polysilicon thin film transistors operated in kink regime. Electronics Letters, 1997, 33, 2075.   | 0.5 | 2         |
| 144 | Boron-enhanced diffusion in excimer laser annealed Si. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2004, 114-115, 114-117.  | 1.7 | 2         |

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|-----|---|-----|-----------|
| 145 | Silicon dioxide deposited by ECR-PECVD for low-temperature Si devices processing. <i>Microelectronics Reliability</i> , 2005, 45, 879-882.  | 0.9 | 2         |
| 146 | Boron distribution in silicon after excimer laser annealing with multiple pulses. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2005, 124-125, 228-231.                                       | 1.7 | 2         |
| 147 | Ultra-shallow junction by laser annealing: Integration issues and modelling. <i>Nuclear Instruments &amp; Methods in Physics Research B</i> , 2006, 253, 1-8.   | 0.6 | 2         |
| 148 | Excimer Laser Annealing for Low-Temperature Polysilicon Thin Film Transistor Fabrication on Plastic Substrates. , 2007, , .   |     | 2         |
| 149 | Asymmetric fingered polysilicon p-channel thin film transistor structure for kink effect suppression. <i>Thin Solid Films</i> , 2007, 515, 7433-7436.   | 0.8 | 2         |
| 150 | Edge Effects in Self-Heating-Related Instabilities in p-Channel Polycrystalline-Silicon Thin-Film Transistors. <i>IEEE Electron Device Letters</i> , 2011, 32, 1707-1709.   | 2.2 | 2         |
| 151 | (Invited) Short Channel Effects and Drain Field Relief Architectures in Polysilicon TFTs. <i>ECS Transactions</i> , 2011, 37, 3-14.   | 0.3 | 2         |
| 152 | A large signal non quasi static compact model for printed organic thin film transistors. , 2016, , .  |     | 2         |
| 153 | Staggered top-gate PDIF-CN2 N-type thin film transistors on flexible plastic substrates. <i>Organic Electronics</i> , 2018, 57, 226-231.  | 1.4 | 2         |
| 154 | Effects of illumination on the electrical characteristics in organic thin-film transistors based on dinaphtho [2,3-b:2â€™,3â€™-f] thieno[3,2-b] thiophene (DNTT): Experiment and modeling. <i>Synthetic Metals</i> , 2022, 2,1 283, 116985. |     | 2         |
| 155 | Properties of amorphous Si: H films prepared by dual ion beam sputtering. <i>Physica Scripta</i> , 1988, 37, 828-830.   | 1.2 | 1         |
| 156 | Short-channel effects in 0.2 $\mu$ m channel length a-Si:H thin-film transistors fabricated by electron beam lithography. <i>Journal of Non-Crystalline Solids</i> , 1991, 137-138, 1225-1228.  | 1.5 | 1         |
| 157 | Instability in hydrogenated amorphous silicon/amorphous silicon dioxide thin-film transistors: Evidence for a predominant effect of charge trapping into the gate insulator. <i>Philosophical Magazine Letters</i> , 1992, 65, 177-182.     | 0.5 | 1         |
| 158 | Comparative analysis of advanced poly-silicon thin-film transistor architectures for drain field relief. , 2003, 5004, 150.   |     | 1         |
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